DMC26604

Silicon NPN epitaxial planar type

For digital circuits

■ Features

- ullet Low collector-emitter saturation voltage $V_{\text{CE(sat)}}$
- Contributes to miniaturization of sets, reduction of component count.
- Eco-friendly Halogen-free package

■ Basic Part Number

Dual DRC2114Y (Individual)

■ Packaging

Embossed type (Thermo-compression sealing): 3000 pcs / reel (standard)

■ Absolute Maximum Ratings $T_a = 25$ °C

Parameter	Symbol	Rating	Unit	
Collector-base voltage (Emitter open)	V_{CBO}	50	V	
Collector-emitter voltage (Base open)	V _{CEO}	50	V	
Collector current	I_{C}	100	mA	
Total power dissipation	P_{T}	300	mW	
Junction temperature	T _j	150	°C	
Storage temperature	T _{stg}	-55 to +150	°C	

■ Package

Code

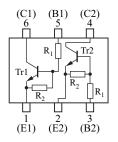
Mini6-G4-B

• Pin Name

1: Emitter (Tr1) 4: Collector (Tr2) 2: Emitter (Tr2) 5: Base (Tr1) 3: Base (Tr2) 6: Collector (Tr1)

■ Marking Symbol: J7

■ Internal Connection



Resistance value	R_1	10	kΩ
	R_2	47	kΩ

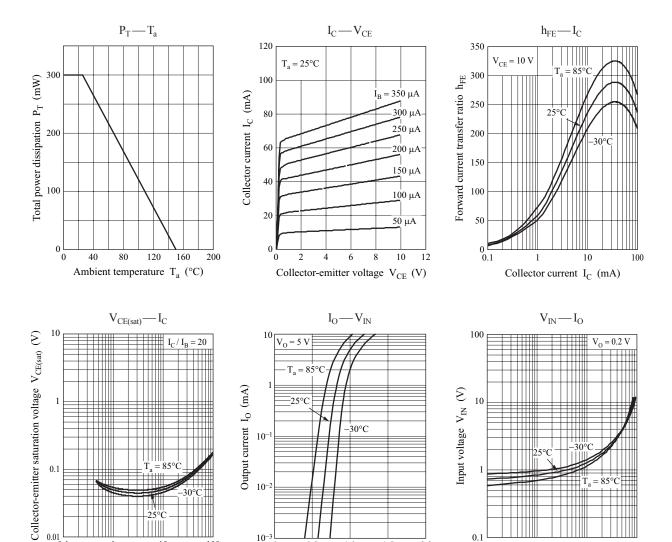
■ Electrical Characteristics $T_a = 25$ °C±3°C

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-base voltage (Emitter open)	V _{CBO}	$I_C = 10 \mu A, I_E = 0$	50			V
Collector-emitter voltage (Base open)	V _{CEO}	$I_C = 2 \text{ mA}, I_B = 0$	50			V
Collector-base cutoff current (Emitter open)	I_{CBO}	$V_{CB} = 50 \text{ V}, I_{E} = 0$			0.1	μΑ
Collector-emitter cutoff current (Base open)	I _{CEO}	$V_{CE} = 50 \text{ V}, I_{B} = 0$			0.5	μΑ
Emitter-base cutoff current (Collector open)	I _{EBO}	$V_{EB} = 6 \text{ V}, I_C = 0$			0.2	mA
Forward current transfer ratio	h_{FE}	$V_{CE} = 10 \text{ V}, I_{C} = 5 \text{ mA}$	80			_
h _{FE} ratio *	h _{FE} (Small/Large)	$V_{CE} = 10 \text{ V, } I_{C} = 5 \text{ mA}$	0.50	0.99		_
Collector-emitter saturation voltage	V _{CE(sat)}	$I_C = 10 \text{ mA}, I_B = 0.5 \text{ mA}$			0.25	V
Input voltage (ON)	V _{I(on)}	$V_{CE} = 0.2 \text{ V}, I_{C} = 5 \text{ mA}$	1.7			V
Input voltage (OFF)	V _{I(off)}	$V_{CE} = 5 \text{ V}, I_{C} = 100 \mu\text{A}$			0.5	V
Input resistance	R_1		-30%	10	+30%	kΩ
Resistance ratio	R_1/R_2		0.17	0.21	0.25	_

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

^{2. *:} Ratio between 2 elements

Panasonic DMC26604



1.0

Input voltage V_{IN} (V)

10-3 _____

100

10

Collector current I_C (mA)

0.1 - 0.1

10

Output current IO (mA)

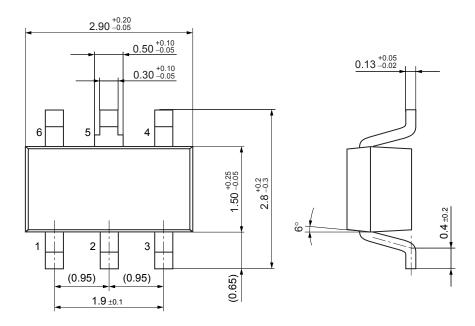
100

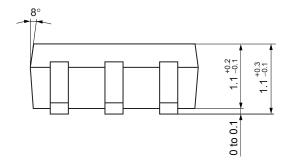
2.0

Ver. CED 2

0.01

Mini6-G4-B Unit: mm





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